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MOSFET – Power, Dual, N-Channel, for 1-Cell Lithium-ion Battery Protection

12 V, 2.85 mΩ, 20 A

This Power MOSFET features a low on-state resistance. This device is suitable for applications such as power switches of portable machines. Best suited for 1–cell lithium-ion battery applications.

Features

- 2.5 V Drive
- Common-Drain Type
- ESD Diode-Protected Gate
- This device is Pb-Free, Halogen Free and RoHS Compliance

Applications

• 1-Cell Lithium-ion Battery Charging and Discharging Switch

Specifications

ABSOLUTE MAXIMUM RATINGS (T_A = 25°C)

Parameter	Symbol	Value	Unit
Source to Source Voltage	V _{SSS}	12	V
Gate to Source Voltage	V _{GSS}	±8	V
Source Current (DC)	۱ _S	20	А
Source Current (Pulse) PW \leq 10 μ s, duty cycle \leq 1%	I _{SP}	80	A
Total Dissipation (Note 1)	PT	1.8	W
Junction Temperature	Tj	150	°C
Storage Temperature	T _{stg}	–55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Value	Unit
Junction to Ambient (Note 1)	R_{\thetaJA}	69.4	°C/W

1. Surface mounted on ceramic substrate (5000 $\text{mm}^2 \times 0.8 \text{ mm}).$

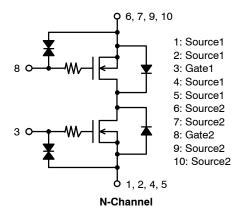


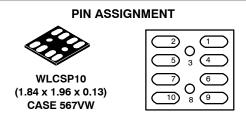
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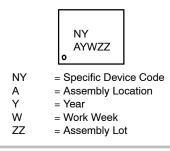
V _{SSS}	R _{SS(ON)} MAX	I _S MAX
12 V	2.85 mΩ @ 4.5 V	20 A
	3.1 mΩ @ 3.8 V	
	4.7 mΩ @ 3.1 V	
	6.8 mΩ @ 2.5 V	

ELECTRICAL CONNECTION





MARKING DIAGRAM



ORDERING INFORMATION

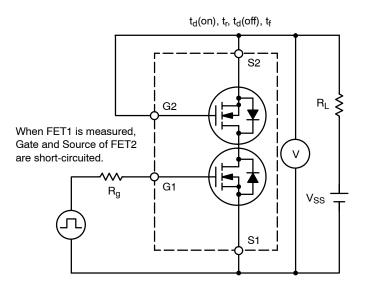
See detailed ordering and shipping information on page 2 of this data sheet.

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{(BR)SSS}	Source to Source Breakdown Voltage	e I _S = 1 mA, V _{GS} = 0 V	12			V
I _{SSS}	Zero-Gate Voltage Source Current	V _{SS} = 10 V, V _{GS} = 0 V			1	μA
I _{GSS}	Gate to Source Leakage Current	$V_{GS} = \pm 8 \text{ V}, \text{ V}_{SS} = 0 \text{ V}$			±1	μΑ
V _{GS} (th)	Gate Threshold Voltage	V _{SS} = 6 V, I _S = 1 mA	0.4		1.3	V
R _{SS} (on)	(on) Static Source to Source On-State Resistance	$I_{S} = 5 \text{ A}, V_{GS} = 4.5 \text{ V}$	1.5	2.2	2.85	mΩ
F		$I_{S} = 5 \text{ A}, V_{GS} = 3.8 \text{ V}$	1.65	2.4	3.1	mΩ
		$I_{S} = 5 \text{ A}, V_{GS} = 3.1 \text{ V}$	1.9	2.8	4.7	mΩ
		$I_{\rm S}$ = 5 A, $V_{\rm GS}$ = 2.5 V	2.0	3.3	6.8	mΩ
t _d (on)	Turn-ON Delay Time	$V_{SS} = 5 V, V_{GS} = 3.8 V, I_{S} = 5 A$		11		μs
t _r	Rise Time	$Rg = 10 k\Omega$ Switching Test Circuit		36		μs
t _d (off)	Turn-OFF Delay Time	7		95		μs
t _f	Fall Time	7		70		μs
Qg	Total Gate Charge	V_{SS} = 5 V, V_{GS} = 3.8 V, I_{S} = 5 A		30		nC
V _{F(S-S)}	Forward Source to Source Voltage	I _S = 3 A, V _{GS} = 0 V		0.75	1.2	V

ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$)

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.





ORDERING INFORMATION

Device	Marking	Package	Shipping [†] (Qty / Packing)
EFC2K107NUZTCG	NY	WLCSOP10, 1.84 x 1.96 x 0.13 (Pb-Free / Halogen Free)	5,000 / Tape & Reel

+ For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

TYPICAL CHARACTERISTICS

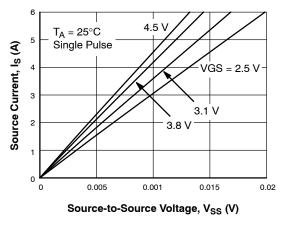
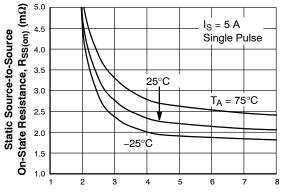


Figure 2. On-Region Characteristics



Gate-to-Source Voltage, V_{GS} (V)

Figure 4. On-Resistance vs. Gate-to-Source Voltage

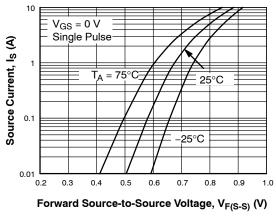


Figure 6. Forward Source-to-Source Voltage vs. Current

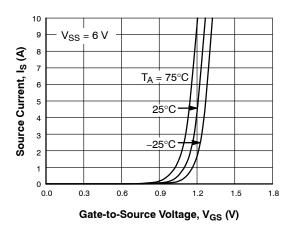
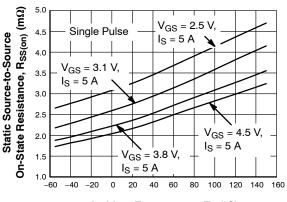


Figure 3. Transfer Characteristics



Ambient Temperature, T_A (°C)



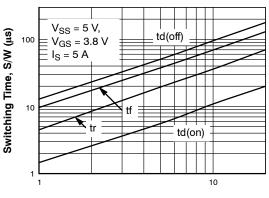




Figure 7. Switching Time vs. Gate Resistance

TYPICAL CHARACTERISTICS

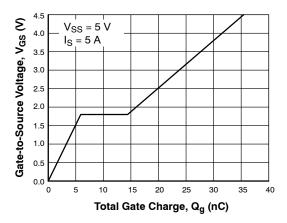


Figure 8. Gate-to-Source Voltage vs. Total Charge

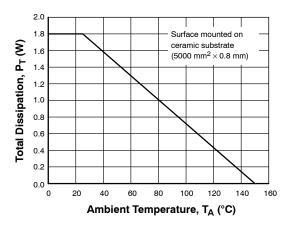


Figure 10. Total Dissipation vs. Temperature

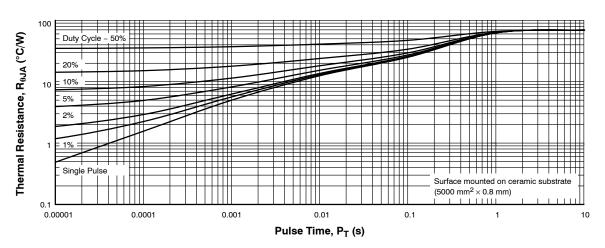


Figure 11. Thermal Response

Note on Usage: Since the EFC2K107NUZ is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

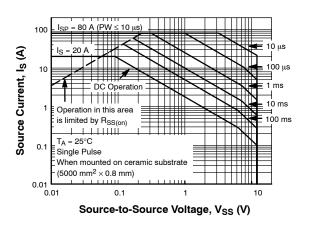
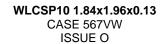
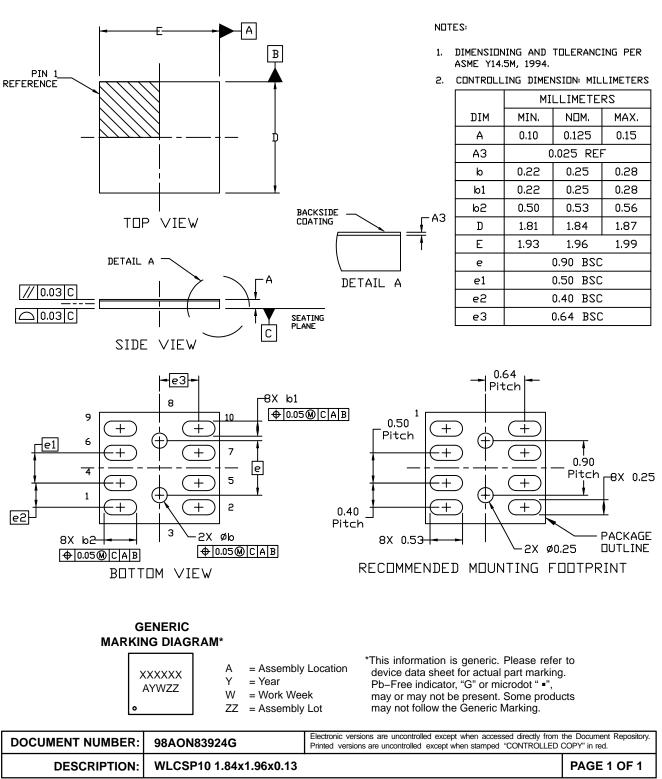


Figure 9. Safe Operating Area





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